
2SC5390

Silicon NPN Epitaxial
High Frequency Amplifier

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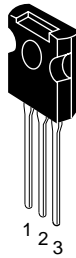
ADE-208-492 (Z)
1st. Edition
December, 1996

Features

- Excellent high frequency characteristics
 $f_T = 1.4\text{GHz}$ (typ.)
- Low output capacitance
 $C_{ob} = 2.4\text{ pF}$ (typ.)
- Isolated package
TO-126FM

Outline

TO-126FM



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings (Ta = 25°C)

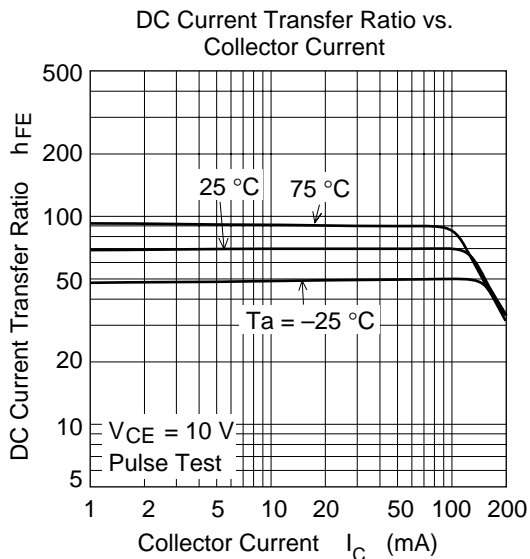
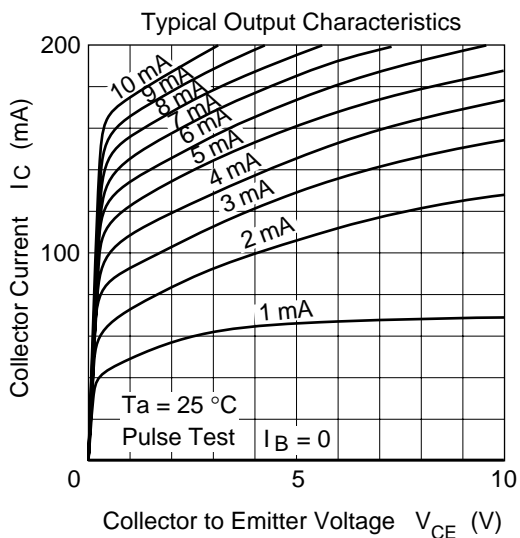
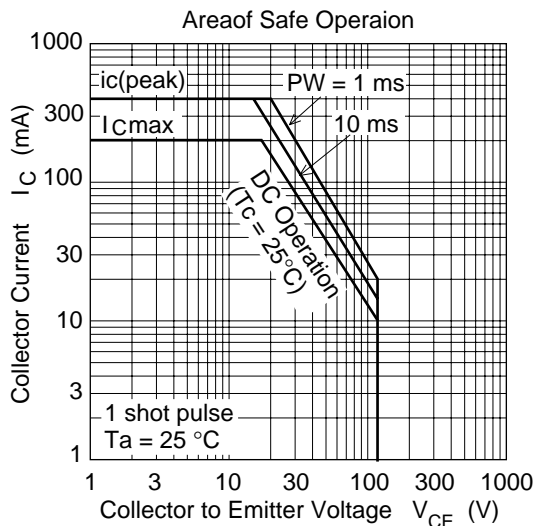
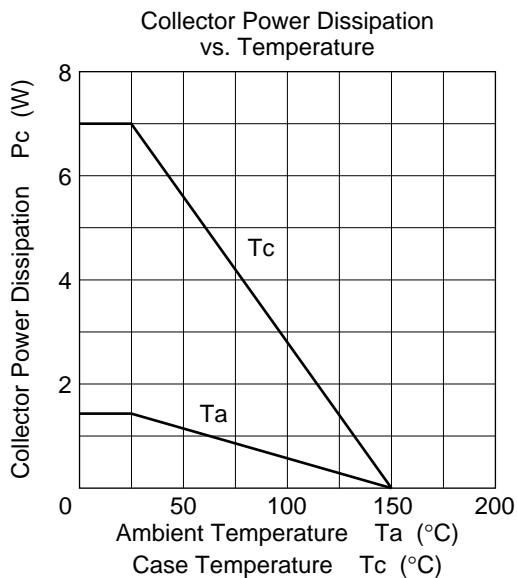
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	110	V
Collector to emitter voltage	V_{CEO}	110	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	200	mA
Collector peak current	$i_{c(peak)}$	400	mA
Collector power dissipation	P_C	1.4	W
Collector power dissipation	P_C^{*1}	7	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Note: 1. Value at $T_c = 25^\circ\text{C}$

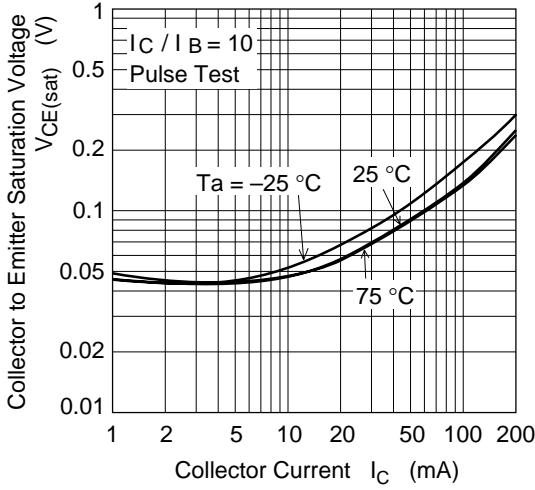
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	110	—	—	V	$I_C = 10\text{E}^{-6}\text{ A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	110	—	—	V	$I_C = 1\text{mA}$, $R_{BE} = \infty$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 100\text{V}$, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 3\text{V}$, $I_C = 0$
DC current transfer ratio	h_{FE}	30	—	100		$V_{CE} = 10\text{ V}$, $I_C = 10\text{mA}$
Base to emitter voltage	V_{BE}	—	—	1	V	$V_{CE} = 10\text{ V}$, $I_C = 10\text{mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1	V	$I_C = 200\text{mA}$, $I_B = 20\text{mA}$
Gain bandwidth product	f_T	1.0	1.4	—	GHz	$V_{CE} = 10\text{ V}$, $I_C = 50\text{mA}$
Collector Output capacitance	C_{ob}	—	2.4	3.5	pF	$V_{CB} = 30\text{V}$, $I_E = 0$ $f = 1\text{MHz}$

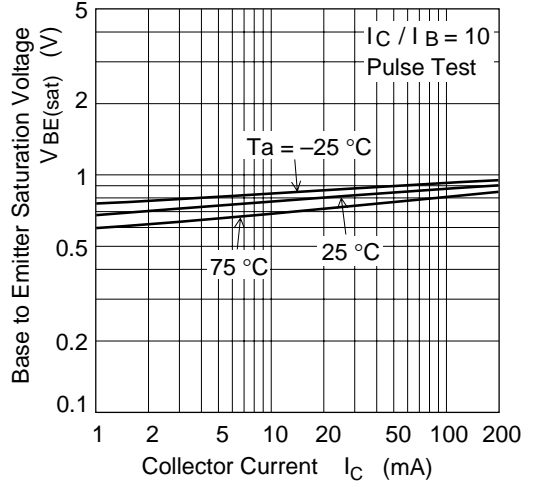
Main Characteristics



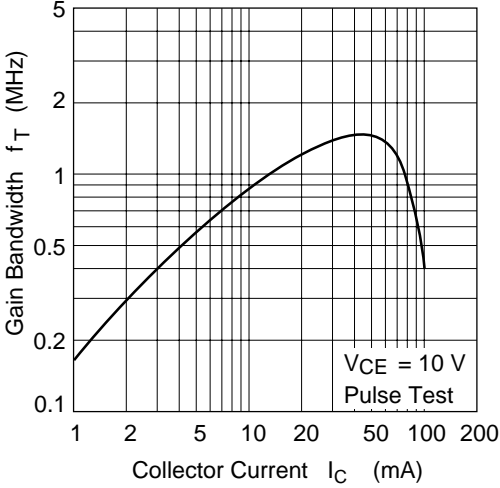
Collector to Emitter Saturation Voltage vs. Collector Current



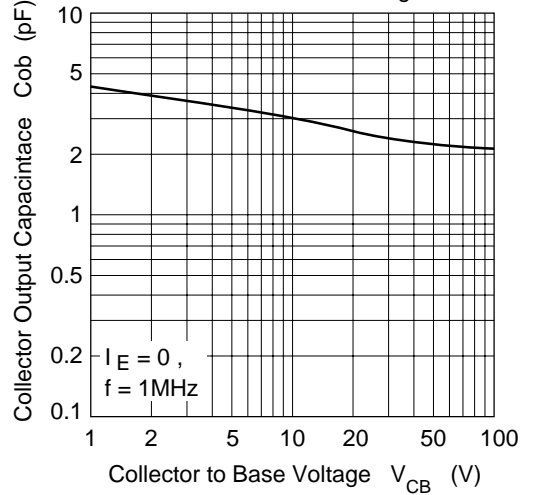
Base to Emitter Saturation Voltage vs. Collector Current



Gain Bandwidth vs. Collector Current

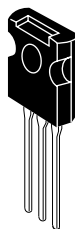
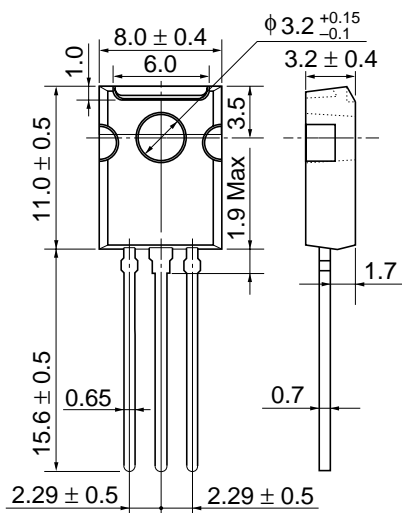


Collector Output Capacitance vs. Collector to Base Voltage



Package Dimensions

Unit: mm



Hitachi Code	TO-126FM
EIAJ	—
JEDEC	—

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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